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(54) **FORMATION OF INTERLAYER INSULATING FILM OF SEMICONDUCTOR DEVICE**

(57) Abstract:

PURPOSE: To form an interlayer insulating film covering a MOS transistor of a titanium silicide structure by suppressing degradation of transistor characteristics and coagulation of titanium silicide film.

CONSTITUTION: A silicon dioxide film 21 is formed by the LPCVD process, a PSG film 31 is formed by the APCVD process using ozone, TEOS, etc., as raw materials, these films are heat-treated in a 750°C nitrogen atmosphere, and a silicon dioxide film 41 is formed by the ECR-PECVD process, and the surface of this silicon dioxide film 41 is polished by the CMP process.

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